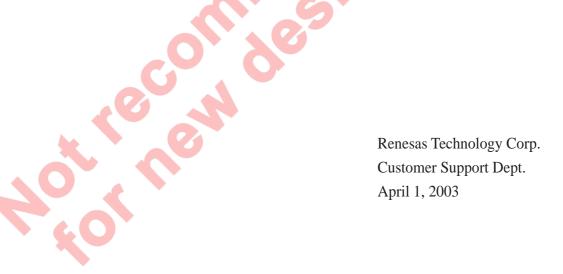
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2SA1485

Silicon PNP Epitaxial

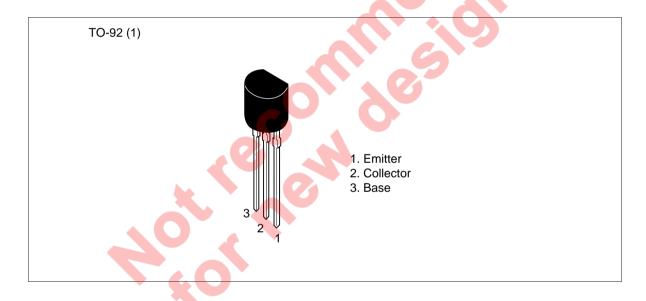


ADE-208-1020 (Z) 1st. Edition Mar. 2001

Application

Low frequency amplifier

Outline



2SA1485

Absolute Maximum Ratings (Ta = 25°C)

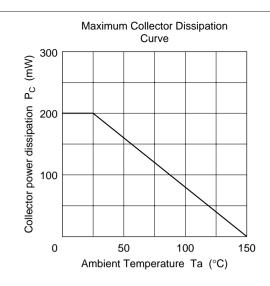
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-200	V
Collector to emitter voltage	V_{CEO}	-200	V
Emitter to base voltage	V_{EBO}	– 5	V
Collector current	I _c	-100	mA
Collector power dissipation	P _c	200	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

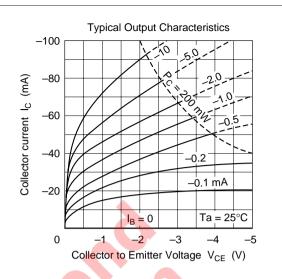
Electrical Characteristics (Ta = 25°C)

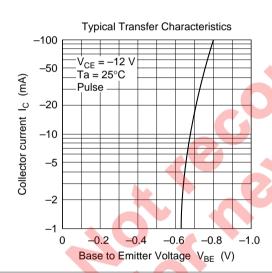
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-200	_		V	$I_{c} = -10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-200	4	_	V	$I_{\rm C} = -0.5$ mA, $R_{\rm BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5		8	V	$I_{E} = -10 \ \mu A, \ I_{C} = 0$
Collector cutoff current	I _{CEO}	E	-	-500	μΑ	V _{CE} = −200 V, R _{BE} = ∞
DC current transfer ratio	h _{FE}	100	+	250		$V_{CE} = -12 \text{ V}, I_{C} = -2 \text{ mA}^{*1}$
Collector to emitter saturation voltage	V _{CE(sat)}	-		-0.5	V	$I_{\rm C} = -30 \text{ mA}, I_{\rm B} = -3 \text{ mA}^{*1}$
Base to emitter voltage	V _{BE}	A	_	-1.0	V	$V_{CE} = -12 \text{ V}, I_{C} = -2 \text{ mA}^{*1}$

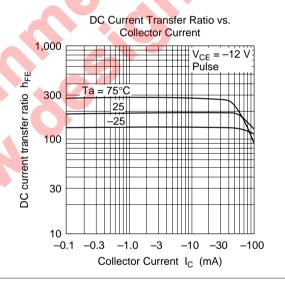
Note: 1. Pulse test

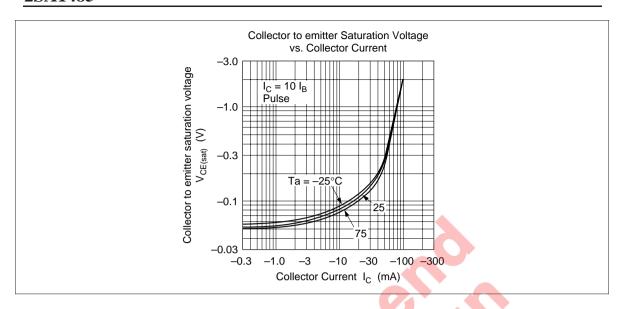




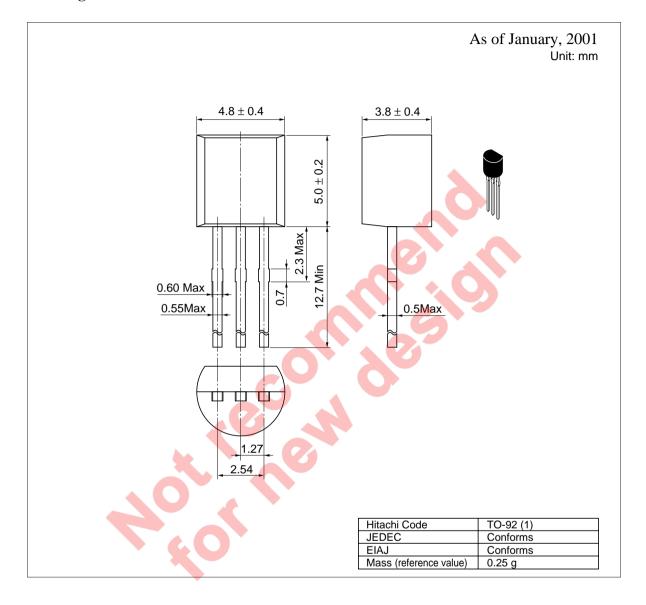








Package Dimensions



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